

IN THE CLAIMS:

1. (currently amended) A semiconductor wafer having at least one region carrying information for identification, characterized in that
the information for identification is provided by magnetic means, wherein the magnetic means comprise a series of magnetic regions and nonmagnetic regions configured to provide a code pattern within the at least one region carrying information for identification.
2. (currently amended) The semiconductor wafer according to claim 1 A semiconductor wafer having at least one region carrying information for identification, characterized in that the information for identification is provided by magnetic means, wherein the magnetic means comprise magnetic ions that are implanted into the semiconductor wafer.
3. (currently amended) The semiconductor wafer according to claim 1, wherein the magnetic means further comprise at least one magnetic film that is placed on at least one surface of the semiconductor wafer.
4. (currently amended) The semiconductor wafer according to claim 1, wherein the magnetic means comprise a series of magnetic regions and nonmagnetic regions, thereby providing a code pattern includes a magnetic bar code pattern.
5. (currently amended) The semiconductor wafer according to claim 1 A semiconductor wafer having at least one region carrying information for identification, characterized in that the information for identification is provided by magnetic means, wherein the magnetic means comprise magnetic regions within the at least one region carrying information for identification having different magnetizations.
6. (original) The semiconductor wafer according to claim 1, wherein the magnetic means are covered with at least one film layer.

7. (original) The semiconductor wafer according to claim 1, wherein the magnetic means are placed near a semiconductor wafer edge.

8. (original) The semiconductor wafer according to claim 1, wherein the magnetic means are placed at an inner region of a semiconductor wafer surface, where a vacuum chuck having magnetic reading capabilities may engage the semiconductor wafer.

9. (currently amended) A method of providing on a semiconductor wafer at least one region carrying information for identification, characterized by the steps of comprising:
- providing a semiconductor wafer; and
- providing the at least one region with magnetic means, wherein the magnetic means are provided in a series of magnetic regions and nonmagnetic regions and configured as a code pattern within the at least one region carrying information for identification.

10. (currently amended) The method according to claim 9 A method of providing on a semiconductor wafer at least one region carrying information for identification, comprising:
providing a semiconductor wafer; and
providing the at least one region with magnetic means, wherein the magnetic means are provided by ion implantation of magnetic ions.

11. (original) The method according to claim 9, wherein the magnetic means are provided by sputtering of magnetic ions.

12. (currently amended) The method according to claim 9, wherein providing the at least one region with magnetic means further comprises depositing a magnetic film on at least one surface of the semiconductor wafer.

13. (currently amended) The method according to claim 9, wherein the magnetic means are further provided in a the series of magnetic regions by direct writing techniques.

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14. (currently amended) The method according to claim 9, wherein the magnetic means are further provided in a the series of magnetic regions by a process of masking of the semiconductor wafer.
15. (currently amended) The method according to claim 9, further comprising the step of covering the magnetic means with at least one film layer.

16-30 (canceled)

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31. (NEW) The semiconductor wafer according to claim 2, wherein the magnetic means are covered with at least one film layer.
32. (NEW) The semiconductor wafer according to claim 2, wherein the magnetic means are proximate a semiconductor wafer edge.
33. (NEW) The semiconductor wafer according to claim 2, wherein the magnetic means are proximate an inner region of a semiconductor wafer surface, where a vacuum chuck having magnetic reading capabilities may engage the semiconductor wafer.
34. (NEW) The semiconductor wafer according to claim 5, wherein the magnetic means are covered with at least one film layer.
35. (NEW) The semiconductor wafer according to claim 5, wherein the magnetic means are proximate a semiconductor wafer edge.
36. (NEW) The semiconductor wafer according to claim 5, wherein the magnetic means are proximate an inner region of a semiconductor wafer surface, where a vacuum chuck having magnetic reading capabilities may engage the semiconductor wafer.

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37. (NEW) The method according to claim 10, further comprising covering the magnetic means with at least one film layer.
